

DERWENT-ACC-NO: 1992-067414

DERWENT-WEEK: 199951

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TITLE: Thin-film FET for memory - has source and  
drain electrodes buried in insulation film between  
upper gate electrode and film covering lower electrode  
NoAbstract Dwg 1/9

PATENT-ASSIGNEE: CASIO COMPUTER CO LTD[CASK]

PRIORITY-DATA: 1990JP-0092021 (April 9, 1990)

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ABSTRACTED-PUB-NO: JP 2969184B

## EQUIVALENT-ABSTRACTS:

Optical disk having a resin substrate has a trench on the periphery  
when the  
resin substrates are adhered to each other. A groove or pit for  
tracking is  
formed on a side of a resin substrate. A 1st ceramics layer, a

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recording  
layer, 2nd ceramics layer and a reflection layer are laminated in  
order. The  
plates are adhered using epoxy gp. resin. A trench is formed at the  
periphery  
and a UV curing type resin is filled into the trench. The resin is  
cured and  
the periphery is cut.

ADVANTAGE - No change of mechanical characteristics at higher temp..

TITLE-TERMS: THIN FILM PET MEMORY SOURCE DRAIN ELECTRODE BURY  
INSULATE FILM

UPPER GATE ELECTRODE FILM COVER LOWER ELECTRODE

NOABSTRACT

DERWENT-CLASS: U11 U12 U13 U14

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